

# 600V ISOLATED HALF BRIDGE GATE DRIVER

4900

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(315) 701-6751

#### **FEATURES:**

- Floating Channels up to 600V
- Up to 8 Amp Peak Source and Sink Current
- · De-Saturation Protection/Shutdown
- · Individual ON, OFF and Soft Shutdown Pins for Each IGBT Gate
- · Undervoltage Lockout
- · Simultaneous Conduction Lockout
- Contact MSK for MIL-PRF-38534 Qualification Status

#### **DESCRIPTION:**

The MSK 4900 is a complete isolated half bridge gate driver hybrid capable of working to 600V channel isolation and 8 amps peak turn-on and turn-off current. Housed in an isolated, convenient bolt-down hermetic package, the MSK 4900 houses the entire isolated DC-DC converter circuitry and opto-isolators for logic signals. The input logic prevents simultaneous conduction by locking out both high side and low side drives in case both inputs are asserted ON at the same time. Each gate drive is capable of sourcing and sinking up to 8 amps peak current. The turn-on and turn-off pins are separate to allow separate gate current control. Upon detection of a de-saturation condition, a FAULT is presented and the transistor is shutdown by a separate controlled shutdown pin. The FAULT will have to be cleared before normal operation will begin again. The MSK 4900 has good thermal conductivity due to an isolated substrate/package design that allows direct heat sinking of the device without insulators.

## **EQUIVALENT SCHEMATIC** DE-SAT SENSE HI HI FAULT GATE HI OFF HI FAULT CLEAR SS HI RETURN HI LOGIC DE-SAT SENSE LO-LO VDD LO FAULT ( GATE LO OFF DRIVE LO VSS LO FAULT CLEAR ( SS LO RETURN LO +15V -5٧ DC-DC +15V CONVERTER -5٧

• Inverter Bridge Gate Drive

· Motor Control Gate Drive Bridge

TYPICAL APPLICATIONS

PIN-OUT INFORMATION

TBD

### **ABSOLUTE MAXIMUM RATINGS**

6

High Voltage Isolation	600V Ts1	Storage Temperature Range65°C to +150°C
Logic Input Voltage	5.5V TL	Lead Temperature Range
Vcc Supply	18V	(10 Seconds)
Continuous Output Current	.TBD Tc	Case Operating Temperature
Peak Ouput Current	. 8A	MSK4900 -40°C to +85°C
Thermal Resistance		MSK4900H/E55°C to +125°C
(output drivers - junction to case)	TJD TJ	Junction Temperature + 150°C

## **ELECTRICAL SPECIFICATIONS**

All Ratings: Tc = +25°C Unless Otherwise Specified

Parameter	Test Conditions	Group A	MSK 4900H/E			MSK 4900			11
		Subgroup	Min.	Тур.	Max.	Min.	Тур.	Max.	Units
Vcc SUPPLY CHARACTERISTICS									
Vcc Voltage	$CL = 0.33 \mu F$ , 20KHz pulse		14.25	15.00	15.75	14.25	15.00	15.75	V
Vcc Current	CL = 0.33μ1 , 20K112 puise		TBD	TBD	TBD	TBD	TBD	TBD	mA
INPUT/OUTPUT LOGIC									
Positive Trigger Input Voltage			2.0	-	-	2.0	-	-	V
Negative Trigger Input Voltage	7		-	-	0.8	-	-	0.8	V
Open Collector Ouput - VOL	IOL = 1.5mA		-	0.15	0.4	-	0.15	0.4	V
Open Collector Ouput - IOL	101-1.01114		-	-	1.5	-	-	1.5	mA
OUTPUT CHARACTERISTICS - GATE DRIVE									
VOH			14.25	15.0	15.75	14.25	15.0	15.75	V
VOL	CL = 0.33µF, 20KHz pulse		-5.75	-5.0	-4.25	-5.75	-5.0	-4.25	V
ЮН			8	-	-	8	-	-	Α
IOL			8	-	-	8	-	-	Α
ISD			TBD	TBD	TBD	TBD	TBD	TBD	μS
tplh - Propagation Delay Time			TBD	TBD	TBD	TBD	TBD	TBD	μS
tphl - Propagation Delay Time			TBD	TBD	TBD	TBD	TBD	TBD	μS
tr - Rise Time			TBD	TBD	TBD	TBD	TBD	TBD	μS
tf - Fall Time			TBD	TBD	TBD	TBD	TBD	TBD	μS
td - De-Sat Delay Time	7		TBD	TBD	TBD	TBD	TBD	TBD	μS
De-Sat Trip Voltage	7		TBD	TBD	TBD	TBD	TBD	TBD	V

### NOTES:

- ① Guaranteed by design but not tested. Typical parameters are representative of actual device performance but are for reference only.
- ② Industrial grade and "E" suffix devices shall be tested to subgroups 1 and 4 unless otherwise specified.
- Military grade devices ("H" Suffix) shall be 100% tested to Subgroups 1, 2, 3 and 4.
- 4) Subgroups 5 and 6 testing available upon request.
  - Subgroup 1, 4 TA = Tc = +25 °C

2, 5 TA = TC = +125°C

3, 6 TA = TC = -55°C

6 Continuous operation at or above absolute maximum ratings may adversly effect the device performance and/or life cycle.

### APPLICATION NOTES

#### MSK 4900 PIN DESCRIPTIONS

VCC - is the bias supply voltage for supplying the input logic and the power supply for the isolated output. This pin should be bypassed to GND with a  $4.7\mu F$  tantalum capacitor and a  $0.1\mu F$  ceramic capacitor as close this pin and GND as possible.

**GND** - is the Vcc supply return for the input logic and the internal isolated supply. This GND is completely isolated from the output section. No output returns should connect to this GND in order to preserve isolation. All Vcc bias supply bypass connections should be made as close to this pin as possible. An input ground plane is the most preferred layout for assuring good, low impedance ground, shielding of inputs from noise, etc.

**HI** - is the input logic pin for commanding the high-side gate drive to turn on. This logic input is TTL compatible. This input is exclusive OR'd with LO to protect against simultaneous turn on of both the high-side and low-side gate drive.

LO - is the input logic pin for commanding the low-side gate drive to turn on. This logic input is TTL compatible. This input is exclusive OR'd with HI to protect against simultaneous turn on of both the high-side and low-side gate drive.

X FAULT - is an open collector output for indicating either a de-saturation condition or an undervoltage condition for the gate drive. This output will be cleared upon activation of X FAULT CLEAR.

**X FAULT CLEAR** - is a logic input pin for clearing a FAULT condition. This input should not be activated until shutdown of the affected gate is complete. Allow (TBD)  $\mu$ Sec after FAULT before activation of this pin.

**X ON** - is the gate drive output pin for turning the gate on. This pin will source TBD current. A separate gate resistor shall be selected to tailor the turn-on characteristics. This pin will turn on to +15V.

NOTE: X = HI or LO

**X OFF** - is the gate drive output pin for turning the gate off. This pin will sink TBD current. A separate gate resistor shall be selected to tailor the turn-off characteristics. This pin will turn off to -5V.

**DE-SAT SENSE X** - is the input connection for sensing desaturation. This pin shall be connected to the collector of the IGBT. This pin is blanked during switching so that it will not false trip.

**X VDD** - is the pin for the floating gate supply voltage. TBD capacitance shall be connected between this pin and X VSS as close to the pin as possible. Nominally, this voltage will be +15V with respect to the RETURN X pin and the emitter of the IGBT.

X VSS - is the return pin for the floating gate supply voltage. TBD capacitance shall be connected between this pin and X VDD as close to the pins as possible. Nominally, this voltage will be -5V with respect to the RETURN X pin and the emitter.

**SS X** - is the soft shutdown pin for slowly turning the gate off after a de-saturation condition. This pin is a separate gate turn-off path and requires a separate gate resistor for this special turn-off approach. The resistor should be sized to keep di/dt from being too high after the de-sat condition.

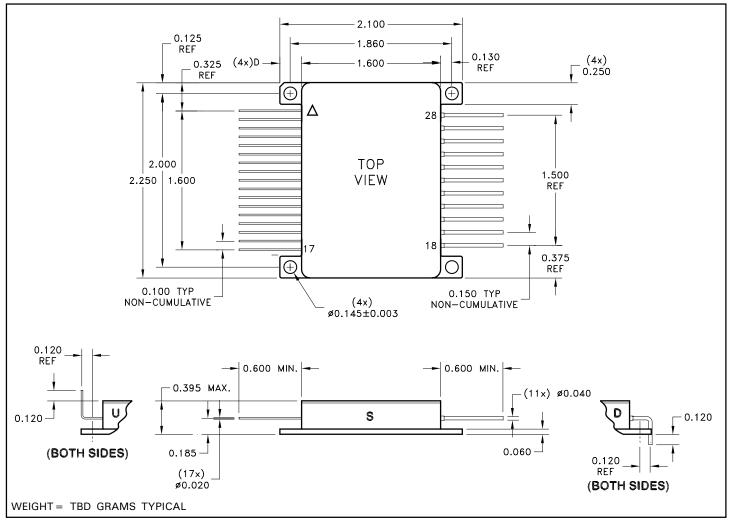
**RETURN X** - is the pin for the emitter reference. This pin will be at zero volts to +15V to -5V for the gate drive voltage.

## TYPICAL APPLICATION

**TBD** 

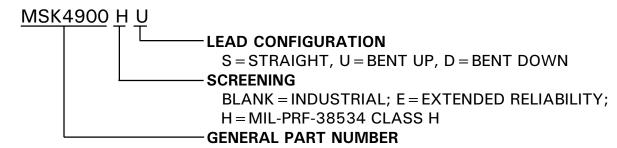
**TBD** 

### **MECHANICAL SPECIFICATIONS**



NOTE: ALL DIMENSIONS ARE  $\pm 0.010$  INCHES UNLESS OTHERWISE LABELED. ESD Triangle indicates Pin 1.

## ORDERING INFORMATION



THE ABOVE EXAMPLE IS A MILITARY GRADE HYBRID WITH LEADS BENT UP.

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